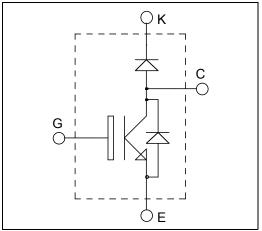
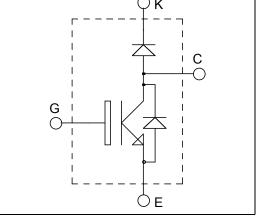


ISOTOP® Boost chopper High speed Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 650V$$

 $I_{C} = 100A*$ @ $Tc = 80°C$





Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- High speed Trench + Field Stop IGBT 4
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- ISOTOP® Package (SOT-227)
- Very low stray inductance

Benefits

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- **RoHS Compliant**



All ratings @ $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings

12000111	· · · · · · · · · · · · · · · · · · ·			
Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		650	V
Ţ	Continuous Collector Current $ \frac{T_C = 25^{\circ}C}{T_C = 80^{\circ}C} $		165*	
I_{C}			100*	Α
I_{CM}	Pulsed Collector Current T	$T_{\rm C} = 25^{\circ}{\rm C}$	270	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation		430	W

^{*} Specification of IGBT device but output current must be limited due to size of output pins.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				50	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C	1.4	1.85	2.3	V
		$I_C = 100A$ $T_j = 150^{\circ}C$		2.2		V	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.6 \text{ mA}$		4.2	5.1	5.6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Condition	ns	Min	Тур	Max	Unit			
Cies	Input Capacitance	$V_{GE} = 0V$			6100					
C_{oes}	Output Capacitance	$V_{CE} = 25V$			232		pF			
C_{res}	Reverse Transfer Capacitance	f = 1MHz			180					
Q_{G}	Gate charge	$V_{GE} = 15V, I_{C} = 100A$ $V_{CE} = 480V$			630		nC			
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	tching (25°C)		19		ns			
T_{r}	Rise Time	$V_{GE} = \pm 15V$			33					
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$ $I_{C} = 100A$			197					
$T_{\rm f}$	Fall Time	$R_G = 3.6\Omega$			21		Ì			
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	tching (150°C)		19					
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			29					
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 400V$ $I_{\text{C}} = 100A$ $R_{\text{G}} = 3.6\Omega$			227		ns			
T_{f}	Fall Time				22					
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150$ °C		2.4		mJ			
E_{off}	Turn off Energy	$I_C = 100A$ $R_G = 3.6\Omega$		-	-	$T_j = 150$ °C		2		1113
R_G	Integrated gate resistor				2		Ω			
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{I}$ $t_p \le 5\mu s ; T_j = 1$			700		A			
R_{thJC}	Junction to Case Thermal Resistance					0.35	°C/W			

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R = 650V$				50	μΑ
I_{F}	DC Forward Current		$Tc = 60^{\circ}C$		50		A
V_{F}	Diode Forward Voltage	$I_F = 50A$	$T_{i} = 25^{\circ}C$		1.6	2	V
		$V_{GE} = 0V$ $I_F = 50A$ $V_R = 300V$ $di/dt = 1800A/\mu s$	$T_i = 150$ °C $T_i = 25$ °C		1.5		
t_{rr}	Reverse Recovery Time		$T_i = 150$ °C		150		ns
-	D D GI		$T_i = 25$ °C		2.6		-
Q_{rr}	Reverse Recovery Charge		$T_{\rm j} = 150^{\circ}{\rm C}$		5.4		μС
E _{rr}	Reverse Recovery Energy	41 40 TOOOT 2 AD	$T_j = 25$ °C		0.6		mJ
L_{rr}	Reverse Recovery Energy		$T_j = 150$ °C		1.2		1113
R_{thJC}	Junction to Case Thermal Resistance					1.14	°C/W



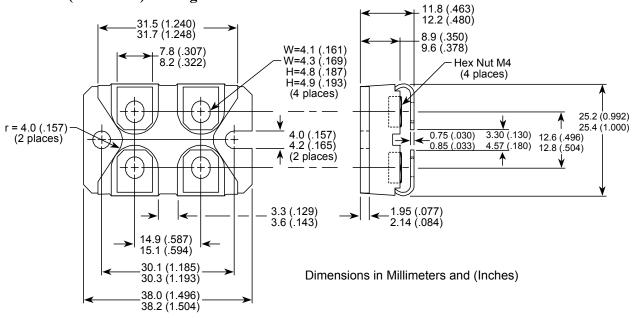
IGBT parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R = 650V$				50	μΑ
I_F	DC Forward Current		$Tc = 60^{\circ}C$		20		A
V_{F}	Diode Forward Voltage	$I_F = 20A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.6	2	V
t_{rr}	Reverse Recovery Time	$I_F = 20A$ $V_R = 300V$ $di/dt = 1600A/\mu s$	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		100 150		ns
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.1		μС
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		0.23 0.50		mJ
R_{thJC}	Junction to Case Thermal Resistance					2.6	°C/W

Thermal and package characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	2500			V
T_{J}, T_{STG}	Storage Temperature Range	-55		175	
T_{JOP}	Recommended junction temperature under switching conditions	-55		T _J max -25	°C
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

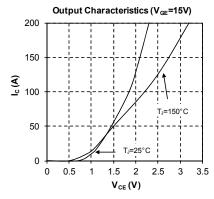
SOT-227 (ISOTOP®) Package Outline

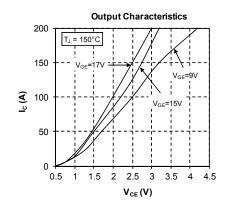


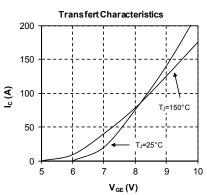
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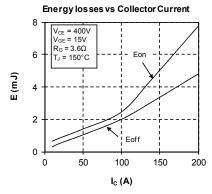


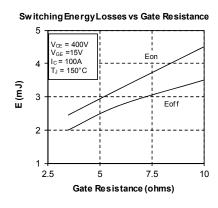
IGBT Typical Performance Curves

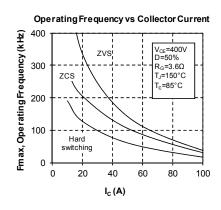


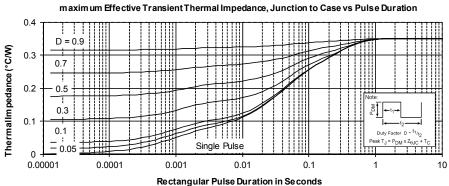










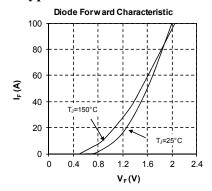


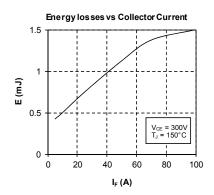
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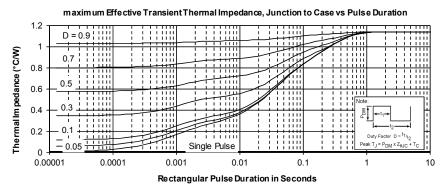
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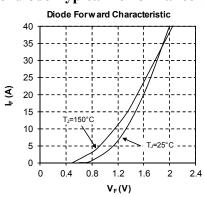
Chopper diode Typical Performance Curves

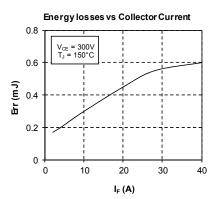


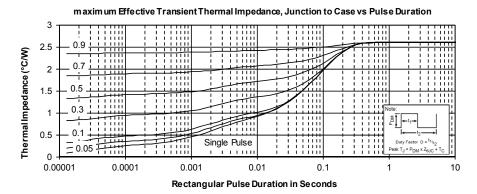




IGBT parallel diode Typical Performance Curves









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